



Product Overview

NTD110N02R: Power MOSFET 24V 110A 4.6 mOhm Single N-Channel DPAK

For complete documentation, see the data sheet

Product Description

Power MOSFET 24V 110A 4.6 mOhm Single N-Channel DPAK

Features

- Planar HD3e Process for Fast Switching Performance
- Body Diode for Low  $t_{rr}$  and  $Q_{rr}$  and Optimized for Synchronous Operation 24 VOLTS
- Low  $C_{iss}$  to Minimize Driver Loss
- Optimized  $Q_{gd} \cdot R_{DS(on)}$  for Shoot-Through Protection
- Low Gate Charge
- Pb-Free Packages are Available

Part Electrical Specifications

Product	Compliance	Status	Channel Polarity	Configuration	$V_{DS(sat)}$ Min (V)	$V_{GS}$ Max (V)	$V_{GS(th)}$ Max (V)	$I_D$ Max (A)	$P_D$ Max (W)	$r_{DS(on)}$ Max @ $V_{GS} = 2.5V$ (m)	$r_{DS(on)}$ Max @ $V_{GS} = 4.5V$ (m)	$r_{DS(on)}$ Max @ $V_{GS} = 10V$ (m)	$Q_g$ Typ @ $V_{GS} = 4.5V$ (nC)	$Q_g$ Typ @ $V_{GS} = 10V$ (nC)	$Q_{gd}$ Typ @ $V_{GS} = 4.5V$ (nC)	$Q_{rr}$ Typ (nC)	$C_{iss}$ Typ (pF)	$C_{oss}$ Typ (pF)	$C_{rss}$ Typ (pF)	Package Type
NTD110N02RT4G	Pb-free Halide free	Active	N-Channel	Single	24	20	2	110	110		6.2	4.6	23.6		11	0.048	2710	1105	450	DPAK-3

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